

Wrocław University of Science and Technology

# Elementy i układy optoelektroniczne





Wrocław University of Science and Technology

HR EXCELLENCE IN RESEARCH

p-contact

# **Elementy i układy** optoelektroniczne

Wstęp

CROSLIGHT Software Inc.

Output aperture

AR coating

Oxide-confined layer

p-DBR

Passivation lay

n-DBR

ctive QWS

GaAs substrate

n-contact

Simulation software by: Crosslight Software Inc.

http://crosslight.com/

Dr inż. Damian Radziewicz

Wrocław 2019



# Wprowadzenie

Informacje o prowadzącym

Informacje o projekcie

Wprowadzenie do APSYS'a



Simulation software by:

Crosslight Software Inc.

http://crosslight.com/



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# Informacje o prowadzącym



Dr inż. Damian Radziewicz

Damian.Radziewicz@pwr.edu.pl

C-2: p. 306, p. 111

M-11: p 138 tel. 4949 (320 4949)

#### Konsultacje:

Poniedziałek: 9<sup>00</sup> – 11<sup>00</sup>, M-11

Piątek: 11<sup>15</sup> – 13<sup>15</sup>, M-11

Projekt Terr	niny
APSYS	<ul> <li>I Raport</li> </ul>
Symulacja struktur testowych	10-12-2019
Symulacja struktur projektowych	
Przygotowanie raportów	
	II Raport
	28-01-2020



# Przykład struktury modelowanej

1  $\mu$ m - Al<sub>0.5</sub>Ga<sub>0.5</sub>As - p=1.0×10<sup>24</sup> m<sup>-3</sup>

0.2 μm - GaAs - undoped; region aktywny

1  $\mu$ m - Al<sub>0.5</sub>Ga<sub>0.5</sub>As - n=1.0×10<sup>24</sup> m<sup>-3</sup>



# **APSYS informacje 1**

#### **APSYS definicja**

**APSYS** is a general purpose 2D/3D modeling software program for semiconductor devices. Based on finite element analysis, it includes many advanced physical models such as hot carrier transport, heterojunction models and thermal analysis. APSYS offers a very flexible and simulation environment for modern semiconductor devices.

**APSYS** can be applied to the modeling and analysis of almost all devices except semiconductor lasers (which are simulated by other products **LASTIP** and **PICS3D**).

These include the following devices based on silicon and compound materials.

- 1. Silicon MOSFET, bipolar transistors and CCD.
- 2. HBT based on SiGe, AlGaAs and InGaAsP.
- 3. GaAs MESFET and Photodectors.
- 4. GaN HEMT.
- 5. Light Emitting Diodes (LED).
- 6. Electro-absorption modulators.
- 7. Organic semiconductor devices (OLED).
- 8. Compound, thin film and multi-junction Solar Cells.



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# **APSYS informacje 2**



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**APSYS** can solve self-consistently the hydrodynamic equations, the heat transfer equations as well as the conventional drift-diffusion equations. Data generated by APSYS include the following:

- 1) Current versus voltage (I-V) characteristics.
- 2) 2D potential, electric field and current distributions.
- 3) 2D distributions of electron and hole concentrations.
- 4) 2D distributions of hot carrier temperatures in the hydrodynamic model.
- 5) 2D distributions of lattice temperature for the heat transfer model.
- 6) Band diagrams under various bias conditions.
- 7) Results of AC small signal analysis for any frequency range. Extraction of 2-port AC parameters such S- and Y- parameters.
- 8) Quantum well subband structure with valence mixing model for quantum devices.
- 9) 2D distributions of occupancy and concentration of deep level traps in a semiconductor.
- 10) 2D optical field distribution for photonic devices such as photodetectors.
- 11) Spontaneous emission spectrum as a function of current for LED's.
- 12) All of the above as a function of time (transient model).
- 13) All of the above at different environment temperatures.





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- .geo The main input file that describe the full details of the device geometry and the initial mesh allocation.
- .sol The main input file that defines the material properties and controls the bias and other conditions of main equation solver.
- .layer An important auxiliary input file that uses the layer structure description to generate the .geo, .doping, .mater and .mplt files,
- .doping which contains doping information that is to be included in the .sol file.
- .mater which contains material information that is to be included in the .sol file.
- .mplt can be used to plot the mesh generated from .geo file.

**APSYS** informacje 3

- .gain file is another important auxiliary input file that can be used to preview the optical gain spectrum, spontaneous emission rate spectrum, quantum well subbands, and other critical physical properties.
   This may be used by the user to do some preliminary estimate before the full simulation is performed.
- .out files may appear as .out 01, .out 02, etc.. These are numerical output data from the main equation solver. They can be used by the .plt program to be plotted. These output files are not meant to be understood by the user.
- .std files may appear as .std 01, .std 02, etc.. These are another form of numerical output data from the main equation solver. They can be used by the CrosslightView program to be displayed in 3D color graphics. These output files can be understood by the user should there were such a need.
- .plt file is used to plot the data in .out output files. APSYS calls the public domain software GNUPLOT to display the graphics in various computer platforms and printers.





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### **APSYS informacje 4**

#### Podstawowa procedura:

- 1. Uruchomić plik "\*.layer", który wygeneruje plik "\*.geo".
- 2. Uruchomić plik "\*.geo", który wygeneruje "mesh".
- 3. Uruchomić główny program z wejściowym plikiem "\*.sol".
- 4. (Opcjonalnie) Wyniki mogą być wykreślone przez CrosslightView. Można to wykonać

przez kliknięcie pliku \*.std w SimuCenter albo w menu: "Action  $\rightarrow$  View Results  $\rightarrow$ 

CrosslightView". Program można również niezależnie uruchomić z menu systemu.







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### **APSYS informacje 6**

Definicja struktury przyrządu – przekrój

1 
$$\mu$$
m - Al<sub>0.5</sub>Ga<sub>0.5</sub>As - p=1.0×10<sup>24</sup> m<sup>-3</sup>

0.2 µm - GaAs - undoped; active region

1 μm - Al<sub>0.5</sub>Ga<sub>0.5</sub>As - n=1.0×10<sup>24</sup> m<sup>-3</sup>





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# **APSYS informacje 6**

#### Definicja struktury przyrządu – plik test1.layer

\$file:test1.layer begin layer column column num=1 w= 0.150000E+01 mesh num=2 r=1. bottom contact column\_num=1 from=0 to= 0.150000E+01 && contact num=1 contact type=ohmic \$ layer\_mater macro\_name=algaas && var symbol1=x var1= 0.500000E+00 && column num=1 layer d= 0.100000E+01 n= 13 && n\_doping1= 0.100000E+25 && r= 0.800000E+00 Ś layer\_mater macro\_name=algaas && var symbol1=x var1= 0.000000E+00 && active macro=AlGaAs && avar symbol1=xw avar1= 0.000000E+00 && column num=1 layer d= 0.200000E+00 n= 5 && shift center= -0.111111E-01 && r= -0.120000E+01 Ś layer mater macro name=algaas && var symbol1=x var1= 0.500000E+00 && column num=1 layer d= 0.100000E+01 n= 11 && p doping1= 0.100000E+25 && r= 0.120000F+01 Ś top contact column num=1 from=0 to= 0.150000E+01 && contact\_num=2 contact\_type=ohmic end\_layer





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# **APSYS informacje 6**

#### Definicja struktury przyrządu – plik test1.layer

\$file:test1.layer
begin\_layer
column column\_num=1 w= 0.150000E+01 mesh\_num=2 r=1.
bottom\_contact column\_num=1 from=0 to= 0.150000E+01 &&
contact num=1 contact type=ohmic

$$1 \ \mu m - AI_{0.5}Ga_{0.5}As - p=1.0 \times 10^{24} \ m^{-3}$$

0.2 μm - GaAs - undoped; active region

#### w = 1.5 μm

column\_num = 1

bottom\_contact
contact\_type = ohmic





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# **APSYS informacje 6**

#### Definicja struktury przyrządu – plik test1.layer

layer\_mater macro\_name=algaas &&
var\_symbol1=x var1= 0.500000E+00 &&
column\_num=1
layer d= 0.100000E+01 n= 13 &&
n\_doping1= 0.100000E+25 &&
r= 0.800000E+00







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### **APSYS informacje 6**

#### Definicja struktury przyrządu – plik test1.layer

layer\_mater macro\_name=algaas && var\_symbol1=x var1= 0.000000E+00 && active\_macro=AlGaAs && avar\_symbol1=xw avar1= 0.000000E+00 && column\_num=1 layer d= 0.200000E+00 n= 5 && shift\_center= -0.111111E-01 && r= -0.120000E+01







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## **APSYS informacje 6**

contact num=2 contact type=ohmic

top contact column num=1 from=0 to= 0.150000E+01 &&

# 1 $\mu$ m - Al<sub>0.5</sub>Ga<sub>0.5</sub>As - p=1.0×10<sup>24</sup> m<sup>-3</sup>

Definicja struktury przyrządu – plik test1.layer

0.2 µm - GaAs - undoped; active region

top contact

contact type = ohmic

1 μm - Al<sub>0.5</sub>Ga<sub>0.5</sub>As - n=1.0×10<sup>24</sup> m<sup>-3</sup>





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### **APSYS informacje 6**

#### Definicja struktury przyrządu – plik test1.layer

\$file:test1.layer begin layer column column num=1 w= 0.150000E+01 mesh num=2 r=1 bottom\_contact column\_num=1 from=0 to= 0.150000E+01 & contact num=1 contact type=ohmic \$ layer\_mater macro\_name=algaas && var symbol1=x var1= 0.500000E+00 && column num=1 layer d= 0.100000E+01 n= 13 && n doning1= 0.100000E+25 && r= 0.800000E+00 layer\_mater macro\_name=algaas && var symbol1=x var1= 0.000000E+00 && active macro=AlGaAs && a avar symbol1=xw avar1= 0.000000E+00 && Ratio=0.8Ratio=1.2 Ratio = -0.8Ratio = -1.2column num=1 layer d= 0.200000E+00 n= 5 && Effects of different ratio on putting mesh points on an edge (a b). shift center= -0.111111E-01 && r= -0.120000E+01 Ś layer mater macro name=algaas && var symbol1=x var1= 0.500000E+00 && column num=1 layer d= 0.100000E+01 n= 11 && p\_doping1= 0.100000E+25 && mesh lines dla kolumn. r= 0.120000E+01 top contact column num=1 from=0 to= 0.150000E+01 && mesh lines dla layer. contact num=2 contact type=ohmic end\_layer



